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(54) Title: PROCEDURE FOR DRYING SILICON

(57) Abstract

The invention relates to a procedure applicable for drying substrate surfaces of a large number of materials, such as semiconductors, metals, plastics and, in particular, silicon. The silicon (1) is dipped into a liquid bath (2) and the silicon (1) is separated from the liquid (3), the liquid of the bath (2) consisting of an aqueous HF solution (3) with a concentration between .001 and 50 %. By adding a gas mixture containing O_2/O_3 immediately after the drying process is finished, the silicon surface is hydrophilized. By adding a gas mixture containing O_2/O_3 during the drying process, cleaning takes place as the ozone enters the solution on the liquid surface.

